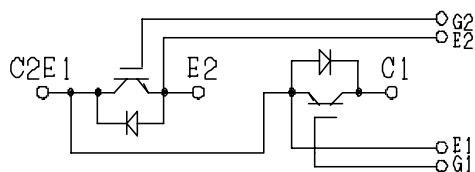


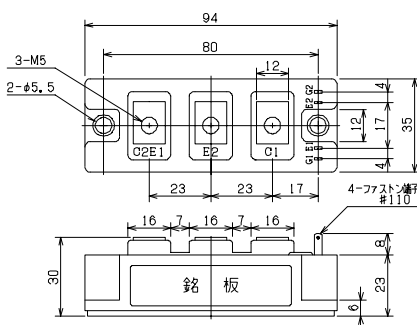
IGBT MODULE Dual 50A 600V

PDMB50A6

CIRCUIT



OUTLINE DRAWING



4-fasten- tab No 110

Dimension(mm)

Approximate Weight : 220g

MAXIMUM RATINGS (Tc=25°C)

Item		Symbol	PDMB50A6	Unit
Collector-Emitter Voltage		V_{CES}	600	V
Gate - Emitter Voltage		V_{GES}	+/- 20	V
Collector Current	DC	I_C	50	A
	1 ms	I_{CP}	100	
Collector Power Dissipation		P_C	250	W
Junction Temperature Range		T_j	-40 to +150	°C
Storage Temperature Range		T_{stg}	-40 to +125	°C
Isolation Voltage (Terminal to Base AC, 1 min.)		V_{ISO}	2500	V
Mounting Torque	Module Base to Heatsink	F_{TOR}	2	N•m
	Bus Bar to Main Terminals			

ELECTRICAL CHARACTERISTICS (T_c=25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Emitter Cut-Off Current		ICES	VCE=600V,VGE=0V	-	-	1.0	mA
Gate-Emitter Leakage Current		IGES	VGE=+/- 20V,VCE=0V	-	-	1.0	μA
Collector-Emitter Saturation Voltage		VCE(sat)	IC=50A,VGE=15V	-	2.0	2.5	V
Gate-Emitter Threshold Voltage		VGE(th)	VCE=5V,IC=50mA	4.0	-	8.0	V
Input Capacitance		Cies	VCE=10V,VGE=0V,f=1MHz	-	5,000	-	pF
Switching Time	Rise Time	tr	VCC= 300V	-	0.15	0.3	μs
	Turn-on Time	ton	RL= 6 ohm	-	0.25	0.4	
	Fall Time	tf	RG= 15.1 ohm	-	0.2	0.35	
	Turn-off Time	toff	VGE= +/- 15V	-	0.45	0.7	

FREE WHEELING DIODES RATINGS & CHARACTERISTICS (Tc=25°C)

Item	Symbol	Rated Value	Unit
Forward Current	DC	50	A
	1 ms	100	

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Peak Forward Voltage	V_F	$I_F=50A, V_{GE}=0V$	-	1.9	2.4	V
Reverse Recovery Time	t_{rr}	$I_F=50A, V_{GE}=-10V, di/dt=50A/\mu s$	-	0.15	0.25	μs

THERMAL CHARACTERISTICS

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Thermal Impedance	IGBT	$R_{th(j-c)}$	Junction to Case	-	-	0.5	°C/W
	DIODE			-	-	1.0	

PDMB50A6

Fig.1- Output Characteristics (Typical)

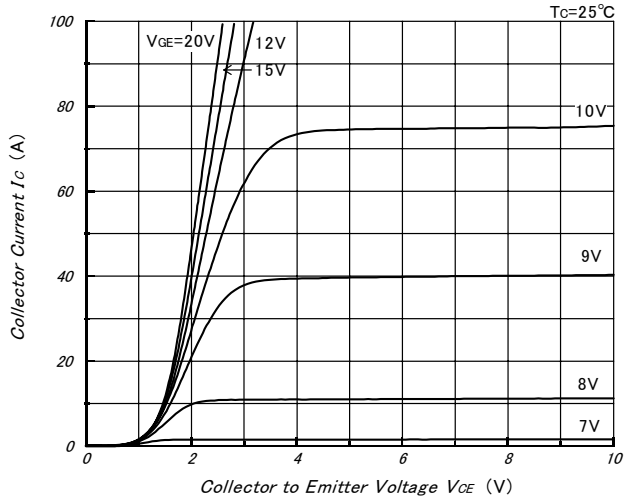


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

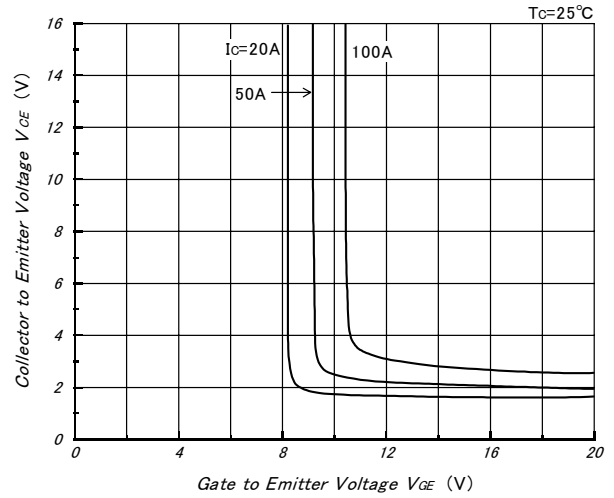


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

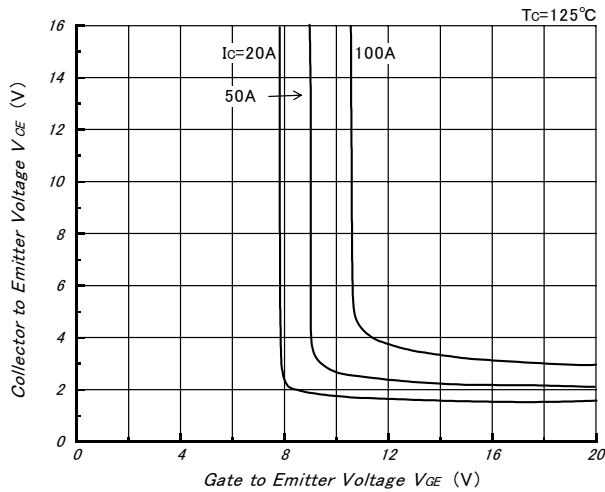


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

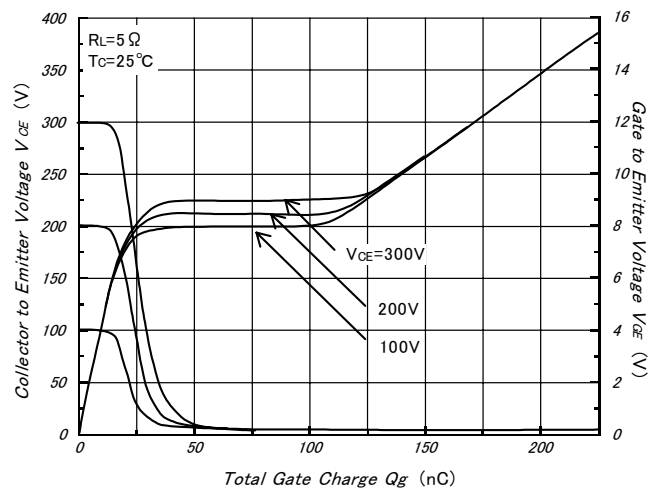


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

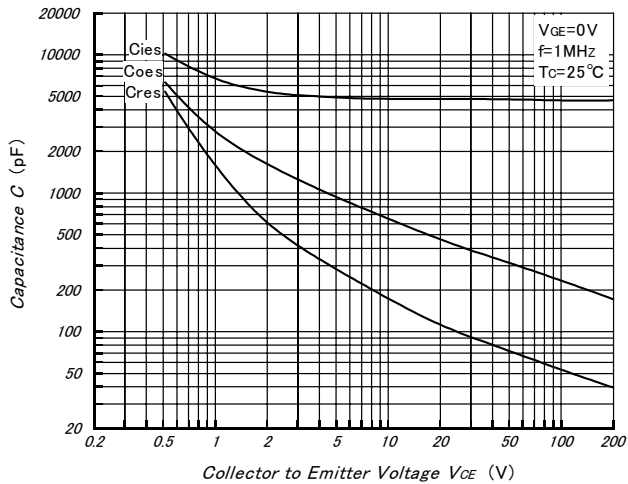
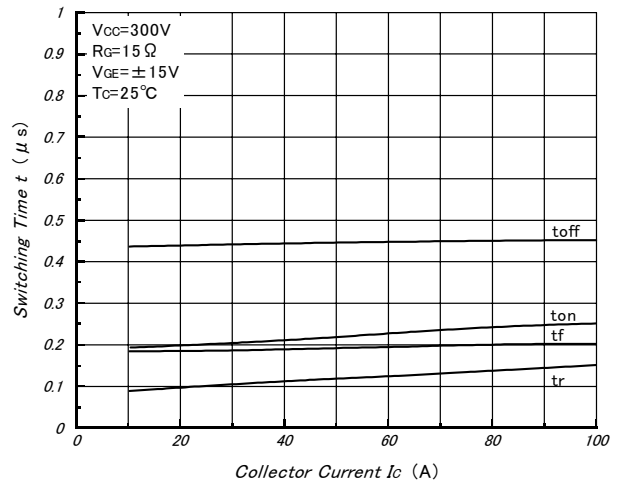


Fig.6- Collector Current vs. Switching Time (Typical)



PDMB50A6

Fig.7- Series Gate Impedance vs. Switching Time (Typical)

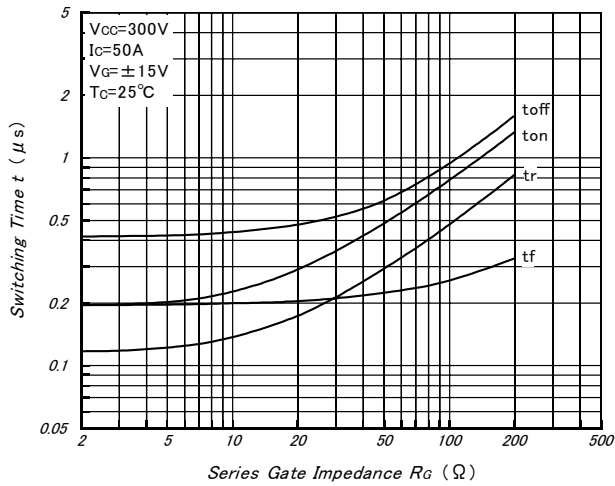


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

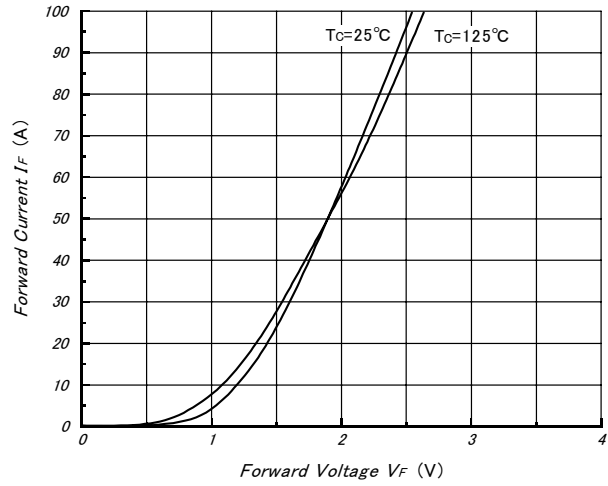


Fig.9- Reverse Recovery Characteristics (Typical)

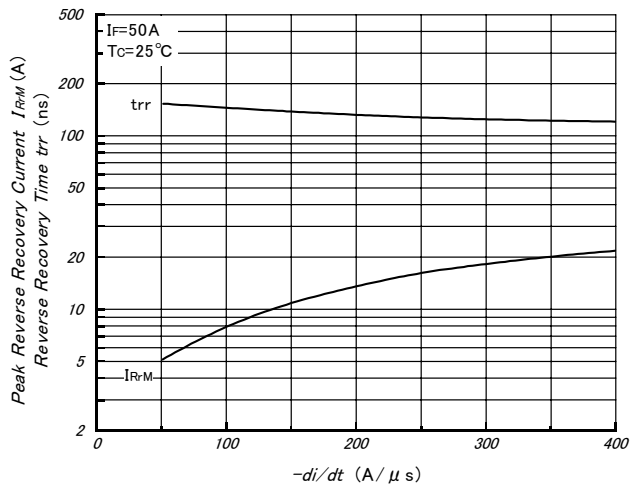


Fig.10- Reverse Bias Safe Operating Area (Typical)

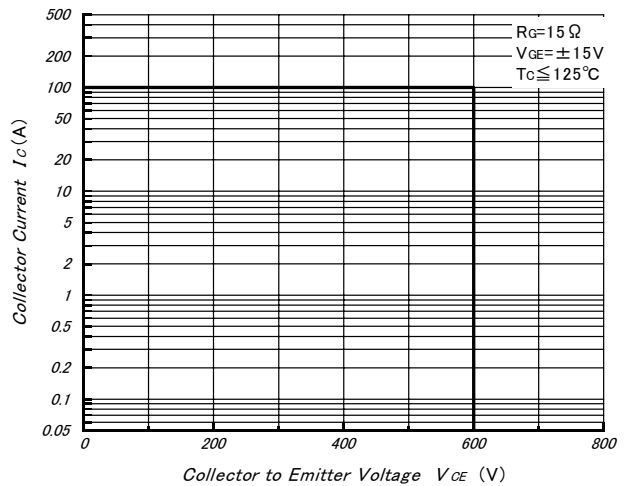


Fig.11- Transient Thermal Impedance

